

AMENDMENTS TO THE ABSTRACT

Please replace the abstract with the following amended abstract:

A layer transfer technique semiconductor apparatus in which a portion of a donor wafer is doped with positively charged hydrogen ions and positively charged helium ions before it is bonded to a portion of a handle wafer. Furthermore, the bonded wafers are annealed at one of two annealing temperatures, which determines whether the wafers are separated using a thermal cleave or a mechanical cleave process.